L Number	Hits	Search Text	DB	Time stamp
-	92	@ad<=19980907 and 'ferroelectric transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:35
-	1	"4047214".PN.	USPAT	2002/09/09 09:51
-	1	"4161038".PN.	USPAT	2002/09/09 09:51
-	1	"5424238".PN.	USPAT	2002/09/09 09:51
-	1	"5654568".PN.	USPAT	2002/09/09 09:52
-	1	"3808674".PN.	USPAT	2002/09/09 10:02
-	1	"5146299".PN.	USPAT	2002/09/09 10:02
-	1	"5361225".PN.	USPAT	2002/09/09 10:02
-	1	"5424238".PN.	USPAT	2002/09/09 10:02
-	3397	((438/3) or (257/295-296)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 10:22
-	2344	(((438/3) or (257/295-296)).CCLS.) and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 14:48
-	1	"4460670".PN.	USPAT	2002/09/09 10:36
-	658	((((438/3) or (257/295-296)).CCLS.) and @ad<=19980907) and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 10:46
-	1	"5530668".PN.	USPAT	2002/09/09 11:09
-	1	"5530667".PN.	USPAT	2002/09/09 11:09
-	1	"5317533".PN.	USPAT	2002/09/09 11:10
-	1	"5289408".PN.	USPAT	2002/09/09 11:10
-	0	@ad<=19980907 and 'ferroelectric transistor' with surrounding adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 15:42
-	0	@ad<=19980907 and 'ferroelectric' with surrounding adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 11:58
-	31	@ad<=19980907 and 'ferroelectric' and 'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:08
-	1191	((257/324) or (257/410-411)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 14:48
-	954	(((257/324) or (257/410-411)).CCLS.) and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 14:58
-	46	((((257/324) or (257/410-411)).CCLS.) and @ad<=19980907) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 14:58
-	45	@ad<=19980907 and 'gate dielectric' with 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 15:47

—	311	@ad<=19980907 and ferroelectric near transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 08:52
—	2	@ad<=19980907 and 'gate insulator' with 'ferroelectric' and 'polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 08:57
—	7813	@ad<=19980907 and 'polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 11:56
—	79	(@ad<=19980907 and 'polysilicon gate') and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 12:04
—	13	@ad<=19980907 and 'ferroelectric transistor' and 'diode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 11:46
—	1149	@ad<=19980907 and 'stacked gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 11:02
—	14	(@ad<=19980907 and 'stacked gate') and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 11:02
—	477	@ad<=19980907 and 'doped polysilicon gates'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 11:58
—	6	@ad<=19980907 and 'polysilicon gates' with 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 12:05
—	6	@ad<=19980907 and 'polysilicon gates' with 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 12:06
—	3	@ad<=19980907 and 'polysilicon gates' with ferroelectric with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 12:11
—	1041	@ad<=19980907 and ferroelectric with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 12:12
—	6	@ad<=19980907 and ferroelectric with 'polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 12:12
—	1264	((257/324) or (257/410-411)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 14:49

-	162	(438/239).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 15:08
-	4	(("5731608") or ("5932904")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 15:09
-	331	(438/3).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 15:33
-	512	(257/295).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:12
-	1614	(257/296).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 15:35
-	269	(257/300).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 15:40
-	220	(257/756).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 15:40
-	92	@ad<=19980907 and 'ferroelectric transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:25
-	485	@ad<=19980907 and 'gate' same 'N' adj1 'doped' same 'P' adj1 'doped'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 16:11
-	5	@ad<=19980907 and 'gate' same 'N' adj1 'doped' same 'P' adj1 'doped' and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 16:11
-	18	@ad<=19980907 and 'polysilicon gate' same 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 16:12
-	31	@ad<=19980907 and 'ferroelectric' and 'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:08
-	385	(257/310).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:13
-	596	(257/288).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:14

-	668	(257/197).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:24
-	255	(257/51).CCLS. and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:25
-	2	("5831301").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:36
-	2	("5759907").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:37
-	2	("5331196").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:37
-	2	("5770875").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:38
-	2	("5904507").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:38
-	2	("5331196").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:39
-	2	("5811869").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:39
-	2	("5786240").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:39
-	2	("5780323").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:40
-	2	("5717230").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:40
-	2	("5502326").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:40
-	2	("5324681").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:41

		2	("5266829").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:41
—		2	("4943538").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 13:41

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